

- **Low $r_{DS(on)}$:**
 0.25 Ω Typ (Full H-Bridge)
 0.4 Ω Typ (Triple Half H-Bridge)
- **Pulsed Current . . . 4 A Per Channel**
- **Matched Sense Transistors for Class A-B Linear Operation**
- **Fast Commutation Speed**

description

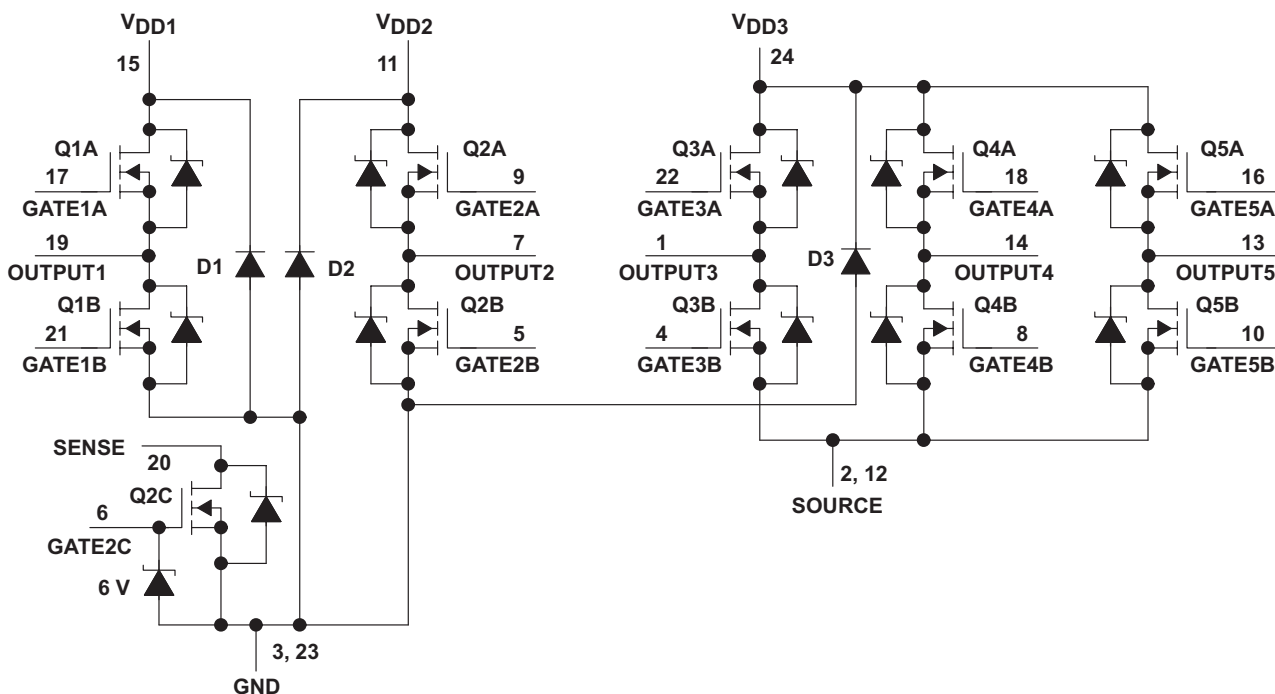
The TPIC1502 is a monolithic power DMOS array that consists of ten electrically isolated N-channel enhancement-mode power DMOS transistors, four of which are configured as a full H-bridge and six as a triple half H-bridge. The lower stage of the full H-bridge is provided with an integrated sense-FET to allow biasing of the bridge in class A-B operation.

The TPIC1502 is offered in a 24-pin wide-body surface-mount (DW) package and is characterized for operation over the case temperature range of -40°C to 125°C .

**DW PACKAGE
(TOP VIEW)**

OUTPUT3	1	24	V _{DD3}
SOURCE	2	23	GND
GND	3	22	GATE3A
GATE3B	4	21	GATE1B
GATE2B	5	20	SENSE
GATE2C	6	19	OUTPUT1
OUTPUT2	7	18	GATE4A
GATE4B	8	17	GATE1A
GATE2A	9	16	GATE5A
GATE5B	10	15	V _{DD1}
V _{DD2}	11	14	OUTPUT4
SOURCE	12	13	OUTPUT5

schematic



- NOTES:
- A. Terminals 3 and 23 must be externally connected.
 - B. Terminals 2 and 12 must be externally connected.
 - C. No output may be taken greater than 0.5 V below GND.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

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TPIC1502

QUAD AND HEX POWER DMOS ARRAY

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absolute maximum ratings, $T_C = 25^\circ\text{C}$ (unless otherwise noted)[†]

Supply-to-GND voltage	20 V
Source-to-GND voltage (Q3A, Q4A, Q5A)	20 V
Output-to-GND voltage	20 V
Sense-to-GND voltage	20 V
Gate-to-source voltage range, V_{GS} (Q1A, Q1B, Q2A, Q2B, Q3A, Q3B, Q4A, Q4B, Q5A, Q5B)	± 20 V
Gate-to-source voltage, V_{GS} (Q2C)	-0.7 V to 6 V
Continuous gate-to-source zener-diode current (Q2C)	± 10 mA
Pulsed gate-to-source zener-diode current (Q2C)	± 50 mA
Continuous drain current, each output (Q1A, Q1B, Q2A, Q2B)	1.5 A
Continuous drain current, each output (Q3A, Q3B, Q4A, Q4B, Q5A, Q5B)	1.5 A
Continuous drain current (Q2C)	5 mA
Continuous source-to-drain diode current (Q1A, Q1B, Q2A, Q2B)	1.5 A
Continuous source-to-drain diode current (Q3A, Q3B, Q4A, Q4B, Q5A, Q5B)	1.5 A
Continuous source-to-drain diode current (Q2C)	5 mA
Pulsed drain current, each output, I_{max} (Q1A, Q1B, Q2A, Q2B) (see Note 1 and Figure 24)	4 A
Pulsed drain current, each output, I_{max} (Q3A, Q3B, Q4A, Q4B, Q5A, Q5B) (see Note 1 and Figure 25)	4 A
Pulsed drain current, each output, I_{max} (Q2C) (see Note 1)	20 mA
Continuous total power dissipation, $T_C = 70^\circ\text{C}$ (see Note 2 and Figures 24 and 25)	2.86 W
Operating virtual junction temperature range, T_J	-40°C to 150°C
Operating case temperature range, T_C	-40°C to 125°C
Storage temperature range, T_{stg}	-65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. Pulse duration = 10 ms, duty cycle = 2%
2. Package mounted in intimate contact with infinite heat sink.

electrical characteristics, Q1A, Q1B, Q2A, Q2B, $T_C = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V _{(BR)DSX}	Drain-to-source breakdown voltage	I _D = 250 μA, V _{GS} = 0		20			V
V _{GS(th)}	Gate-to-source threshold voltage	I _D = 1 mA, V _{DS} = V _{GS} , See Figure 5		1.5	1.85	2.2	V
V _{GS(th)match}	Gate-to-source threshold voltage matching	I _D = 1 mA, V _{DS} = V _{GS}				40	mV
V _(BR)	Reverse drain-to-GND breakdown voltage	Drain-to-GND current = 250 μA (D1, D2)		20			V
V _{(BR)GS}	Gate-to-source breakdown voltage, Q2C	I _{GS} = 100 μA		6			V
V _{(BR)SG}	Source-to-gate breakdown voltage, Q2C	I _{GS} = 100 μA		0.7			V
V _{(DS)on}	Drain-to-source on-state voltage	I _D = 1.5 A, V _{GS} = 10 V, See Notes 3 and 4			0.375	0.45	V
V _F	Forward on-state voltage, GND-to-V _{DD1} , GND-to-V _{DD2}	I _D = 1.5 A (D1, D2) See Notes 3 and 4			1.5		V
V _{F(SD)}	Forward on-state voltage, source-to-drain	I _S = 1.5 A, V _{GS} = 0, See Notes 3 and 4 and Figure 19			0.93	1.2	V
I _{DSS}	Zero-gate-voltage drain current	V _{DS} = 16 V, V _{GS} = 0	T _C = 25°C		0.05	1	μA
			T _C = 125°C		0.5	10	
I _{GSSF}	Forward gate current, drain short-circuited to source	V _{GS} = 16 V, V _{DS} = 0			10	100	nA
I _{GSSR}	Reverse gate current, drain short-circuited to source	V _{SG} = 16 V, V _{DS} = 0			10	100	nA
I _{lkg}	Leakage current, V _{DD1} -to-GND, V _{DD2} -to-GND, gate shorted to source	V _{DGND} = 16 V	T _C = 25°C		0.05	1	μA
			T _C = 125°C		0.5	10	
r _{DS(on)}	Static drain-to-source on-state resistance	V _{GS} = 10 V, I _D = 1.5 A, See Notes 3 and 4 and Figure 9	T _C = 25°C		0.25	0.3	Ω
			T _C = 125°C		0.38	0.51	
g _{fs}	Forward transconductance	V _{DS} = 14 V, I _D = 750 mA, See Notes 3 and 4 and Figure 13		0.75	1.2		S
C _{iss}	Short-circuit input capacitance, common source	V _{DS} = 14 V, f = 1 MHz, V _{GS} = 0, See Figure 17		98		pF	
C _{oss}	Short-circuit output capacitance, common source			70			
C _{rss}	Short-circuit reverse transfer capacitance, common source			54			
α _S	Sense-FET drain current ratio	V _{DS} = 6 V,	I _{D(Q2B)} = 1.5 mA	100	150	200	

NOTES: 3. Technique should limit $T_J - T_C$ to 10°C maximum.

4. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.

source-to-drain diode characteristics, Q1A, Q2A, $T_C = 25^\circ\text{C}$

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{rr}	Reverse-recovery time	$I_S = 750\ \text{mA}$, $V_{GS} = 0$, $V_{DS} = 14\ \text{V}$, $di/dt = 100\ \text{A}/\mu\text{s}$, See Figures 1 and 23		18		ns
Q_{RR}	Total diode charge			14		nC

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resistive-load switching characteristics, Q1A, Q1B, Q2A, Q2B, $T_C = 25^\circ\text{C}$

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_{d(on)}$ Turn-on delay time	$V_{DD} = 14\text{ V}$, $R_L = 18.7\ \Omega$, $t_{en} = 10\text{ ns}$, $t_{dis} = 10\text{ ns}$, See Figure 3		12		ns
$t_{d(off)}$ Turn-off delay time			13		
t_r Rise time			2.2		
t_f Fall time			6		
Q_g Total gate charge	$V_{DS} = 14\text{ V}$, $I_D = 750\text{ mA}$, $V_{GS} = 10\text{ V}$, See Figure 4 and Figure 21		1.7	2.1	nC
$Q_{gs(th)}$ Threshold gate-to-source charge			0.3	0.4	
Q_{gd} Gate-to-drain charge			0.4	0.5	
L_D Internal drain inductance			7		nH
L_S Internal source inductance			7		
R_g Internal gate resistance			0.25		Ω

electrical characteristics, Q3A, Q3B, Q4A, Q4B, Q5A, Q5B, $T_C = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)DSX}$ Drain-to-source breakdown voltage	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0$	20			V
$V_{GS(th)}$ Gate-to-source threshold voltage	$I_D = 1\text{ mA}$, $V_{DS} = V_{GS}$, See Figure 6	1.5	1.85	2.2	V
$V_{(BR)}$ Reverse drain-to-GND breakdown voltage	Drain-to-GND current = $250\ \mu\text{A}$ (D3)	20			V
$V_{(DS)on}$ Drain-to-source on-state voltage	$I_D = 1.5\text{ A}$, $V_{GS} = 10\text{ V}$, See Notes 3 and 4		0.6	0.75	V
V_F Forward on-state voltage, GND-to- V_{DD3}	$I_D = 1.5\text{ A}$ (D3), See Notes 3 and 4		1.5		V
$V_{F(SD)}$ Forward on-state voltage, source-to-drain	$I_S = 1.5\text{ A}$, $V_{GS} = 0$, See Notes 3 and 4 and Figure 20		1	1.2	V
I_{DSS} Zero-gate-voltage drain current	$V_{DS} = 16\text{ V}$, $V_{GS} = 0$	$T_C = 25^\circ\text{C}$	0.05	1	μA
		$T_C = 125^\circ\text{C}$	0.5	10	
I_{GSSF} Forward gate current, drain short-circuited to source	$V_{GS} = 16\text{ V}$, $V_{DS} = 0$		10	100	nA
I_{GSSR} Reverse gate current, drain short-circuited to source	$V_{SG} = 16\text{ V}$, $V_{DS} = 0$		10	100	nA
I_{lkg} Leakage current, V_{DD3} -to-GND, gate shorted to source	$V_{DGND} = 16\text{ V}$	$T_C = 25^\circ\text{C}$	0.05	1	μA
		$T_C = 125^\circ\text{C}$	0.5	10	
$r_{DS(on)}$ Static drain-to-source on-state resistance	$V_{GS} = 10\text{ V}$, $I_D = 1.5\text{ A}$, See Notes 3 and 4 and Figure 10	$T_C = 25^\circ\text{C}$	0.4	0.5	Ω
		$T_C = 125^\circ\text{C}$	0.61	0.85	
g_{fs} Forward transconductance	$V_{DS} = 14\text{ V}$, $I_D = 750\text{ mA}$, See Notes 3 and 4 and Figure 14	0.4	0.74		S
C_{iss} Short-circuit input capacitance, common source	$V_{DS} = 14\text{ V}$, $V_{GS} = 0$, $f = 1\text{ MHz}$, See Figure 18		73		pF
C_{oss} Short-circuit output capacitance, common source			65		
C_{rss} Short-circuit reverse transfer capacitance, common source			43		

NOTES: 3: Technique should limit $T_J - T_C$ to 10°C maximum.

4: These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.



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source-to-drain diode characteristics, Q3A, Q4A, Q5A, $T_C = 25^\circ\text{C}$

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{rr} Reverse-recovery time	$I_S = 750\text{ mA}$, $V_{DS} = 14\text{ V}$, See Figures 2 and 23		26		ns
Q_{RR} Total diode charge			17		nC

resistive-load switching characteristics, Q3A, Q3B, Q4A, Q4B, Q5A, Q5B, $T_C = 25^\circ\text{C}$

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$t_{d(on)}$ Turn-on delay time	$V_{DD} = 14\text{ V}$, $R_L = 18.7\ \Omega$, $t_{dis} = 10\text{ ns}$, See Figure 3		13		ns
$t_{d(off)}$ Turn-off delay time			13		
t_r Rise time			3		
t_f Fall time			7		
Q_g Total gate charge	$V_{DS} = 14\text{ V}$, $I_D = 750\text{ mA}$, See Figure 4 and Figure 22		1	1.3	nC
$Q_{gs(th)}$ Threshold gate-to-source charge			0.2	0.25	
Q_{gd} Gate-to-drain charge			0.2	0.25	
L_D Internal drain inductance			7		nH
L_S Internal source inductance			7		
R_g Internal gate resistance			0.25		Ω

thermal resistance

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$R_{\theta JA}$ Junction-to-ambient thermal resistance	See Notes 5 and 8		90		$^\circ\text{C}/\text{W}$
$R_{\theta JB}$ Junction-to-board thermal resistance	See Notes 6 and 8		52		
$R_{\theta JP}$ Junction-to-pin thermal resistance	See Notes 7 and 8		28		

- NOTES:
5. Package mounted on a FR4 printed-circuit board with no heatsink.
 6. Package mounted on a 24 in², 4-layer FR4 printed-circuit board.
 7. Package mounted in intimate contact with infinite heatsink.
 8. All outputs with equal power

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PARAMETER MEASUREMENT INFORMATION

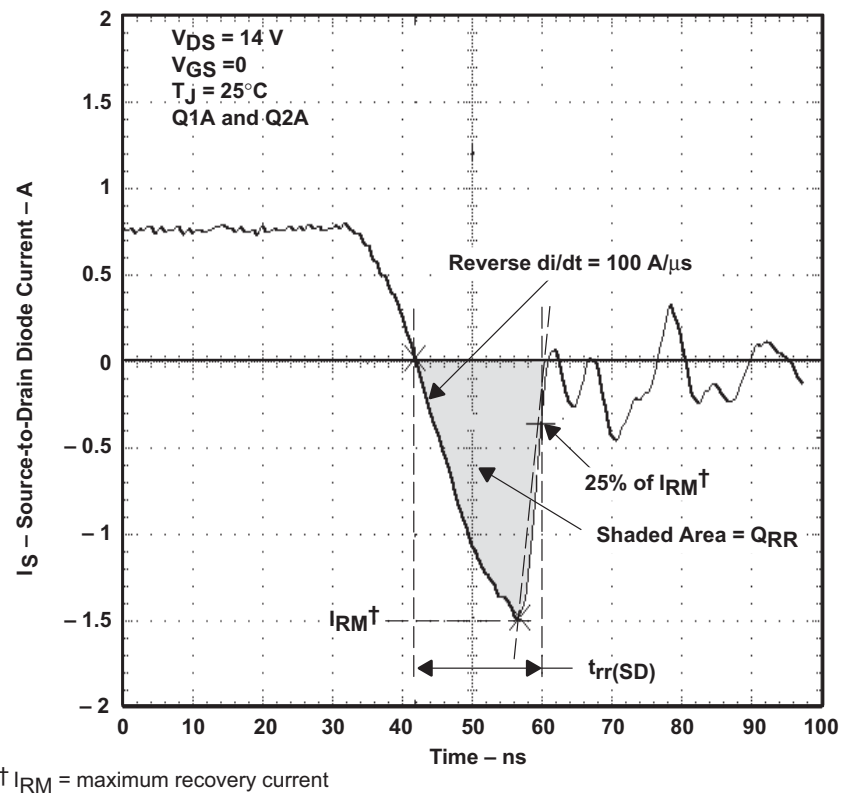
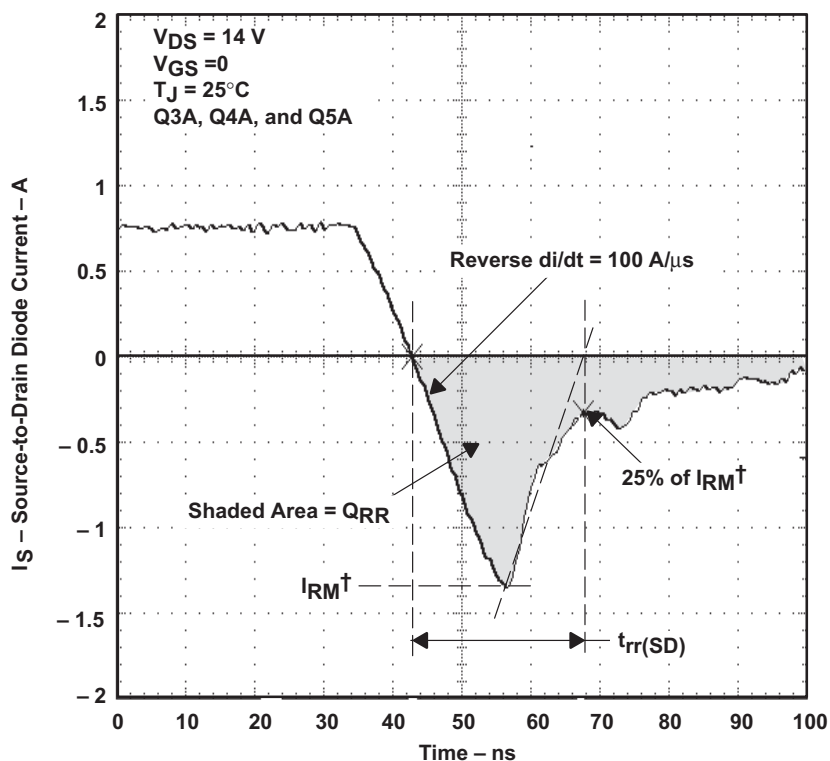


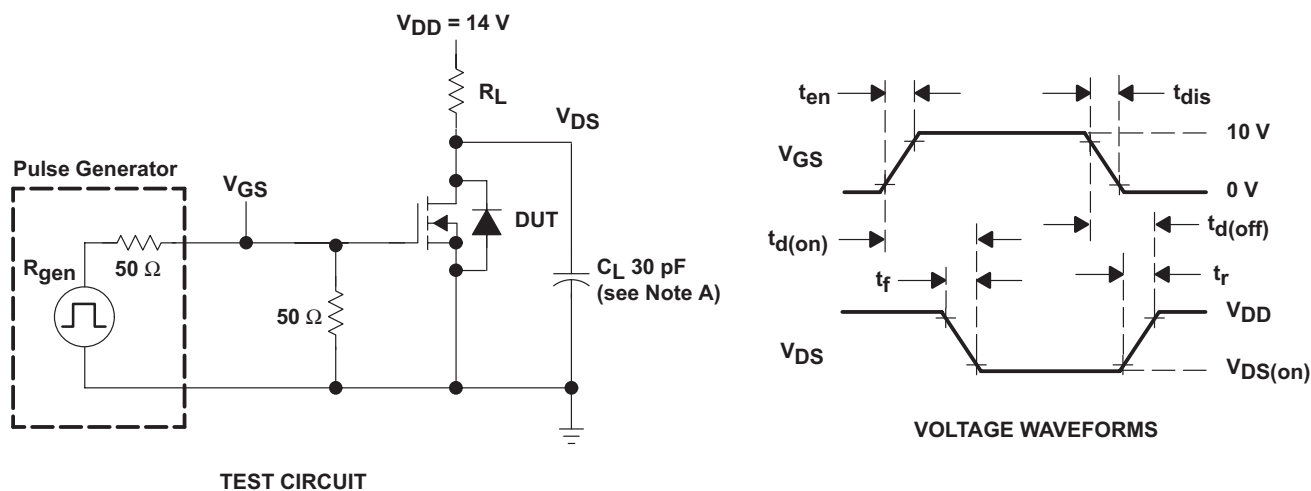
Figure 1. Reverse-Recovery-Current Waveform of Source-to-Drain Diodes

PARAMETER MEASUREMENT INFORMATION



† I_{RM} = maximum recovery current

Figure 2. Reverse-Recovery-Current Waveform of Source-to-Drain Diodes



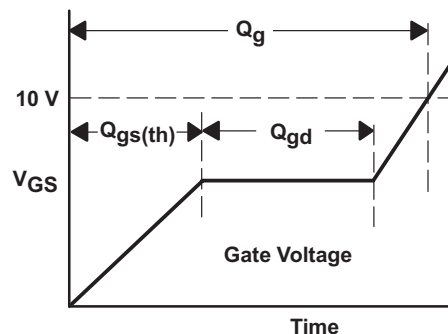
TEST CIRCUIT

NOTE A: C_L includes probe and jig capacitance.

Figure 3. Resistive-Switching Test Circuit and Voltage Waveforms

The diagram shows a circuit for characterizing a DUT as a current source. A 12-V battery is connected to a network of components: a $0.2\ \mu\text{F}$ capacitor in parallel with a $50\ \text{k}\Omega$ resistor. This network is followed by a series combination of a $0.3\ \mu\text{F}$ capacitor and a current regulator. The current regulator consists of a PMOS transistor (gate to source) and an NPN bipolar junction transistor (base to emitter). The emitter of the BJT is connected to a $14\ \text{V}$ supply (V_{DD}). The collector of the BJT is connected to the drain of the PMOS transistor, which is also the output node labeled V_{DS} . The DUT is connected between V_{DS} and ground. A current $I_G = 100\ \mu\text{A}$ is injected into the gate of the PMOS transistor from a pulse source. Two resistors, labeled I_G Current-Sampling Resistor and I_D Current-Sampling Resistor, are connected in series with the gate and drain nodes, respectively, to ground.

TEST CIRCUIT



VOLTAGE WAVEFORM

Figure 4. Gate-Charge Test Circuit and Voltage Waveform

GATE-TO-SOURCE THRESHOLD VOLTAGE vs JUNCTION TEMPERATURE

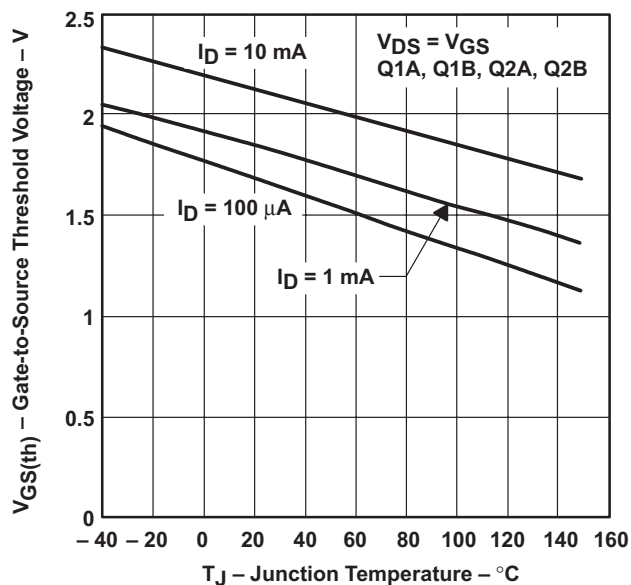


Figure 5

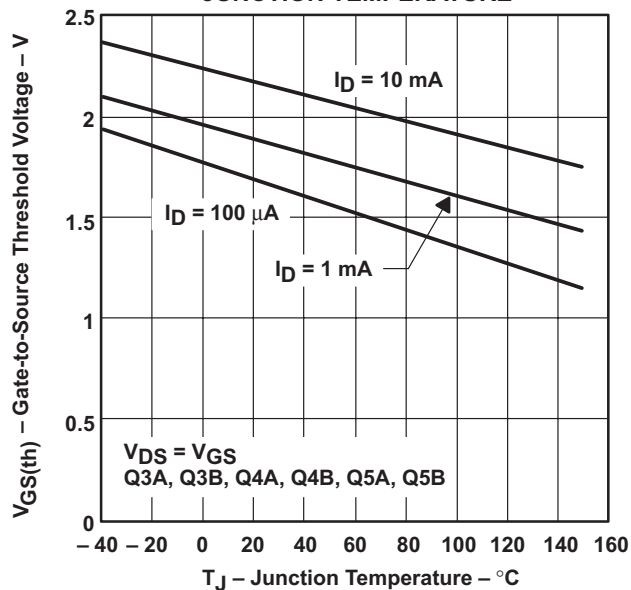


Figure 6

TYPICAL CHARACTERISTICS

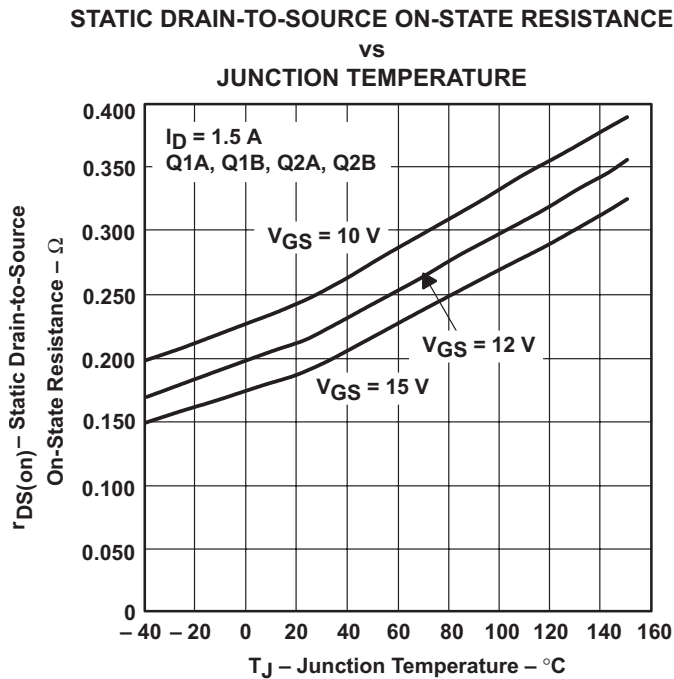


Figure 7

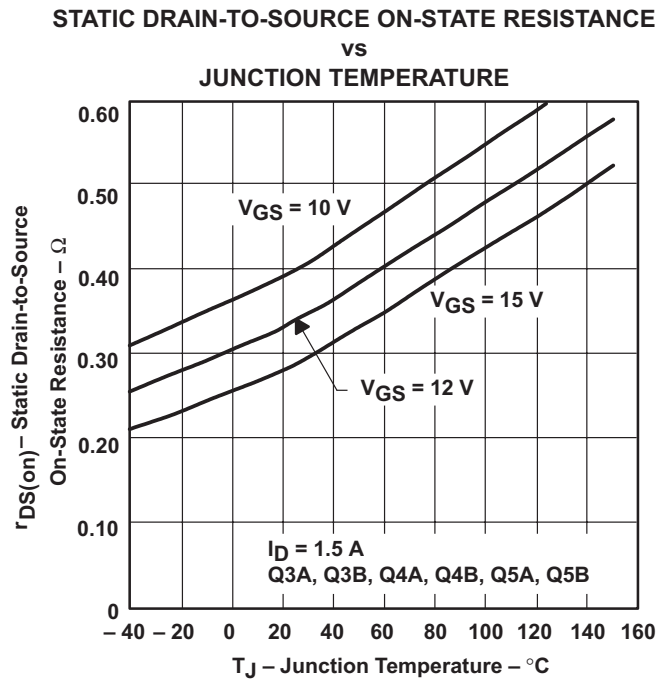


Figure 8

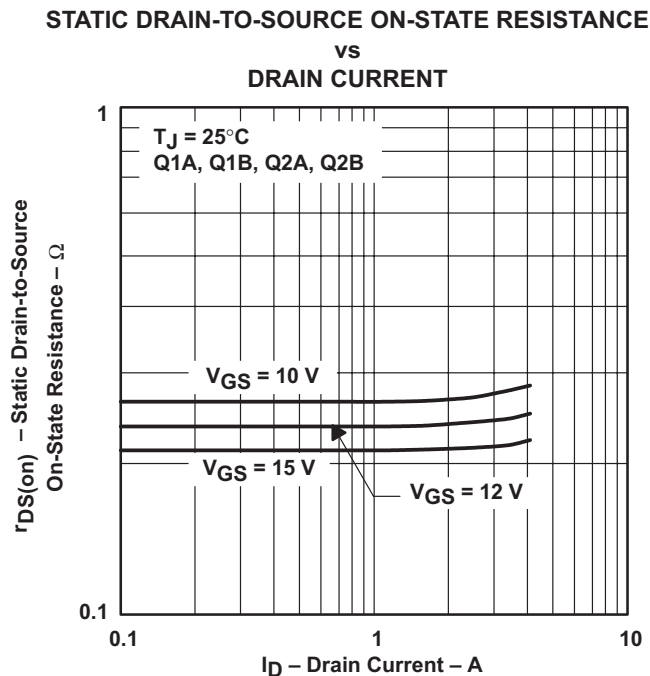


Figure 9

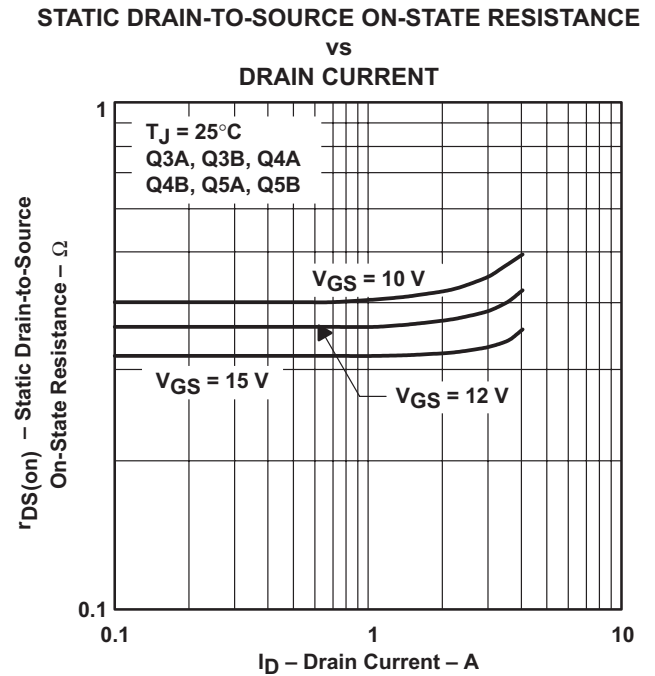


Figure 10

TYPICAL CHARACTERISTICS

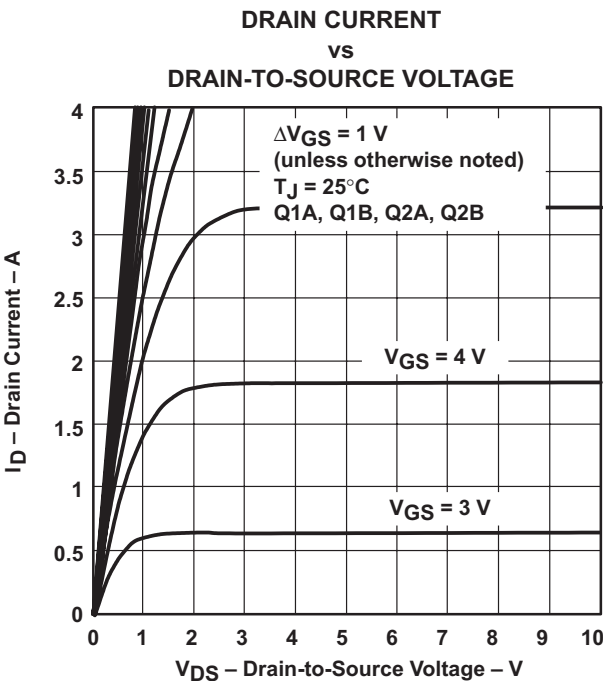


Figure 11

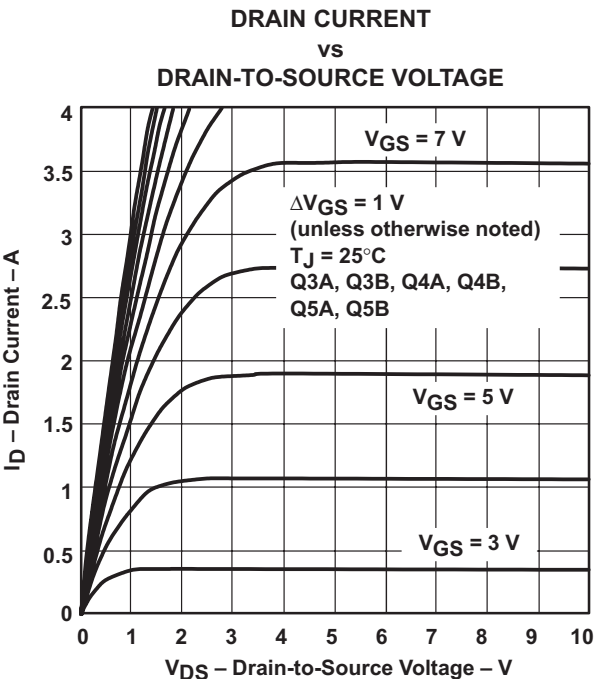


Figure 12

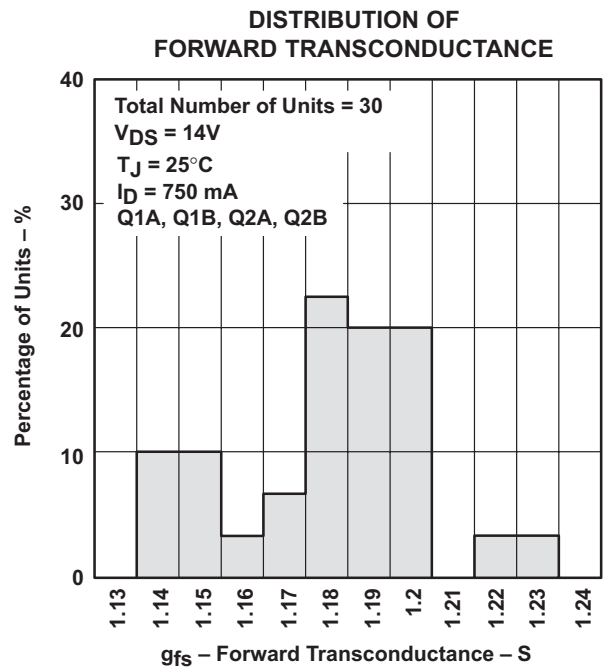


Figure 13

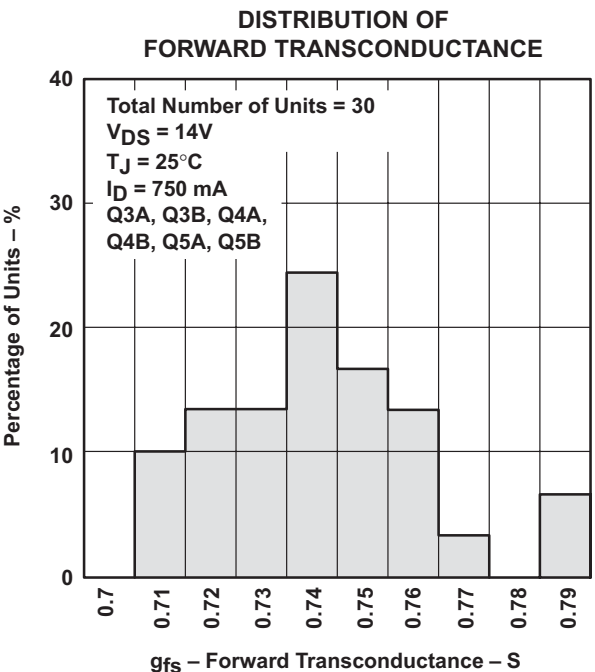


Figure 14

TYPICAL CHARACTERISTICS

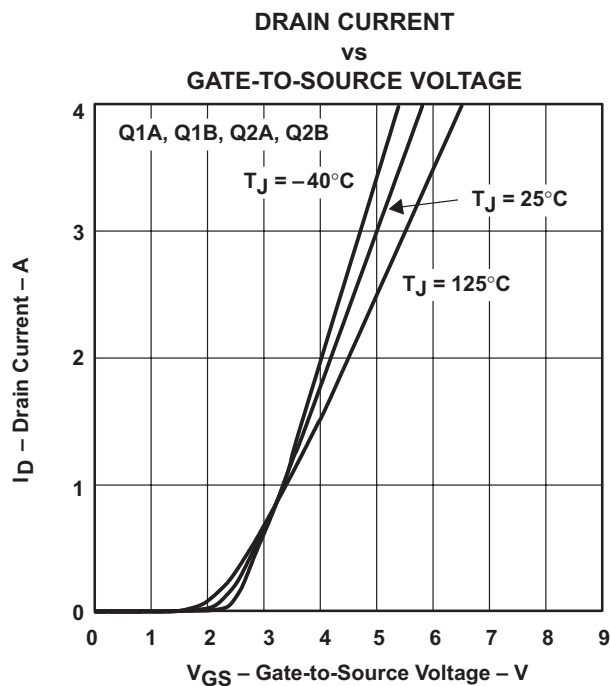


Figure 15

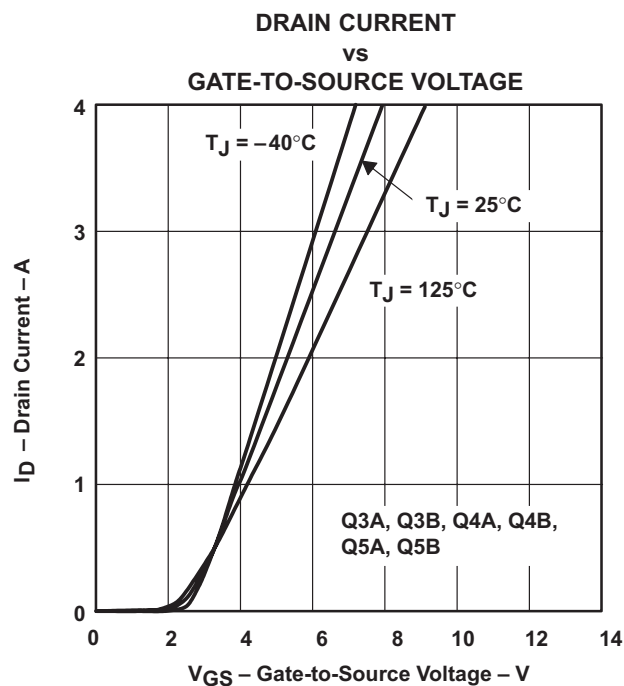


Figure 16

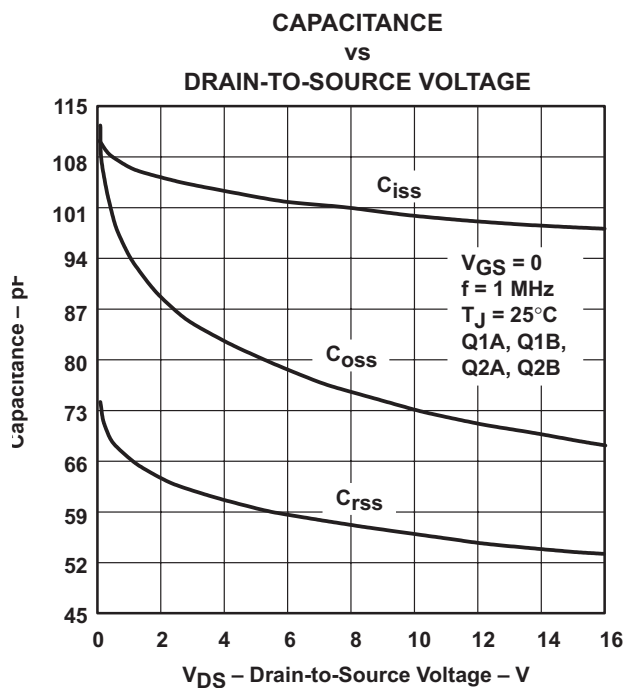


Figure 17

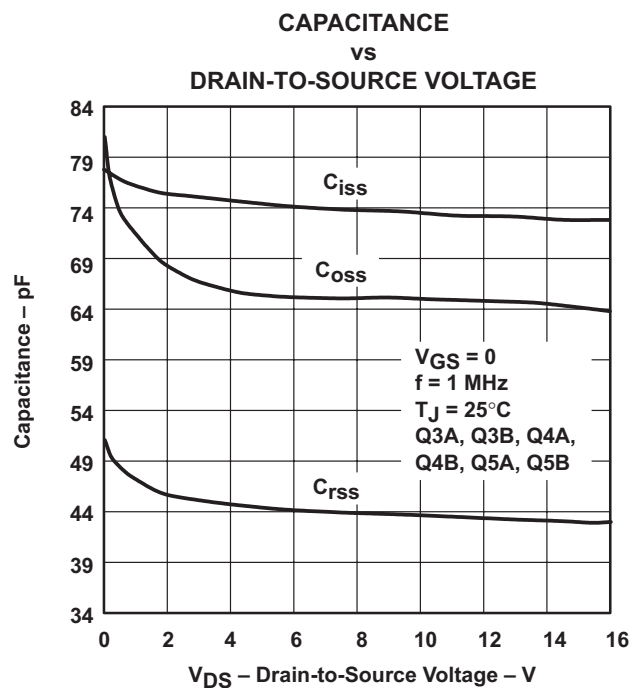


Figure 18

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TYPICAL CHARACTERISTICS

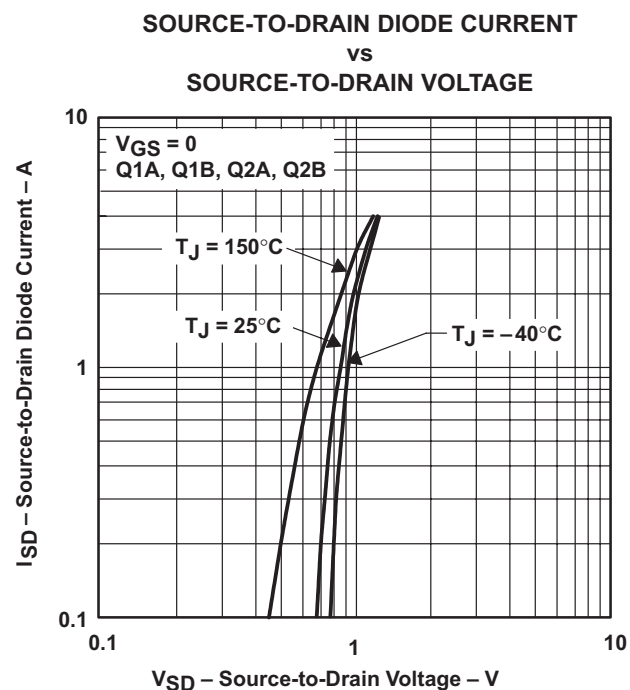


Figure 19

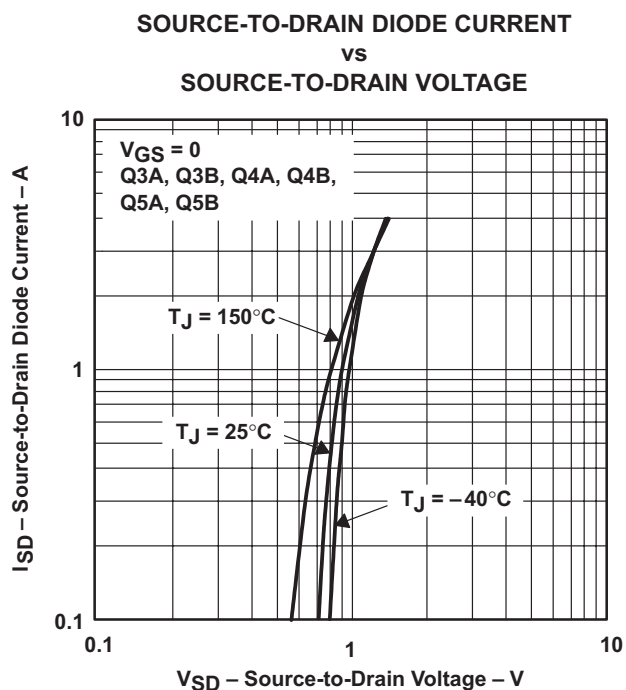


Figure 20

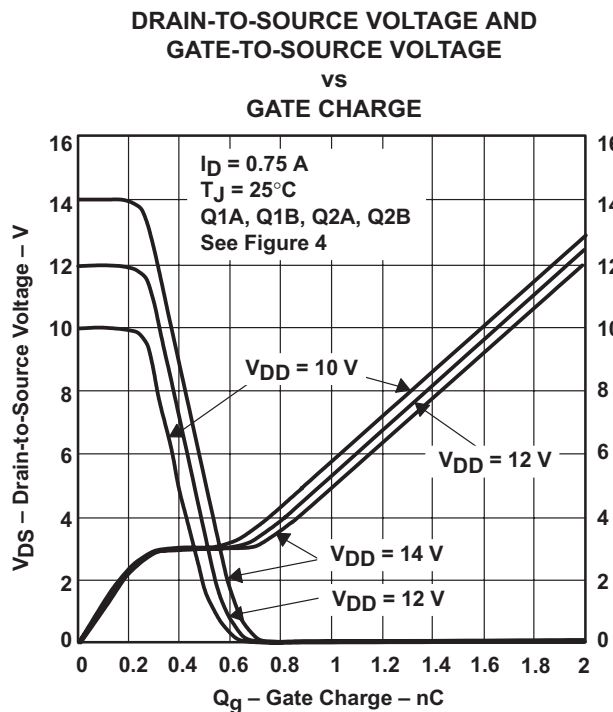


Figure 21

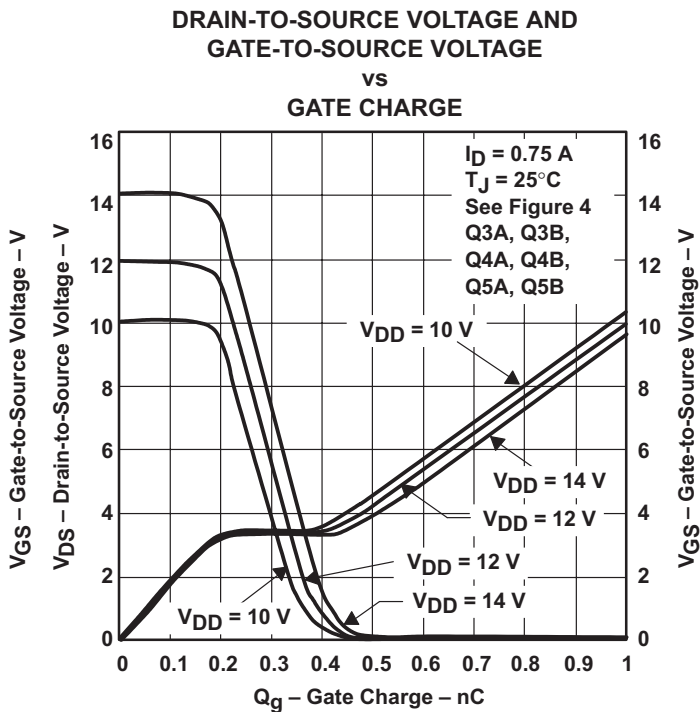


Figure 22

TYPICAL CHARACTERISTICS

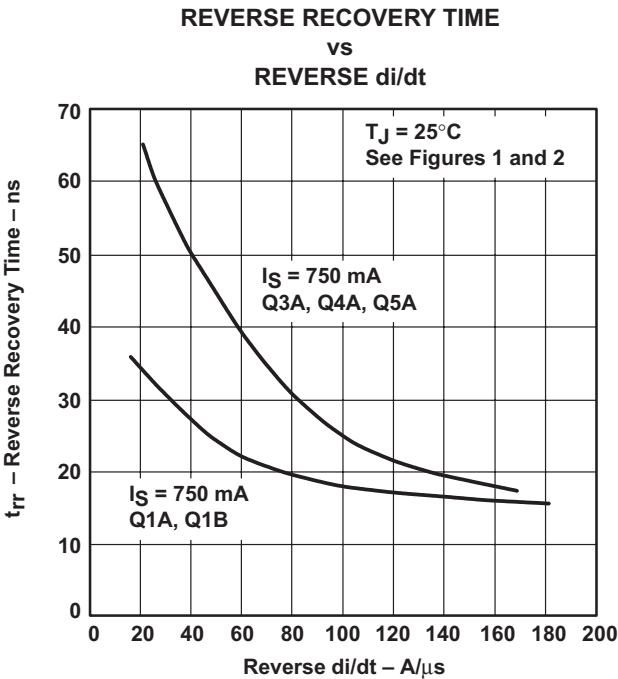


Figure 23



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THERMAL INFORMATION

MAXIMUM DRAIN CURRENT vs DRAIN-TO-SOURCE VOLTAGE

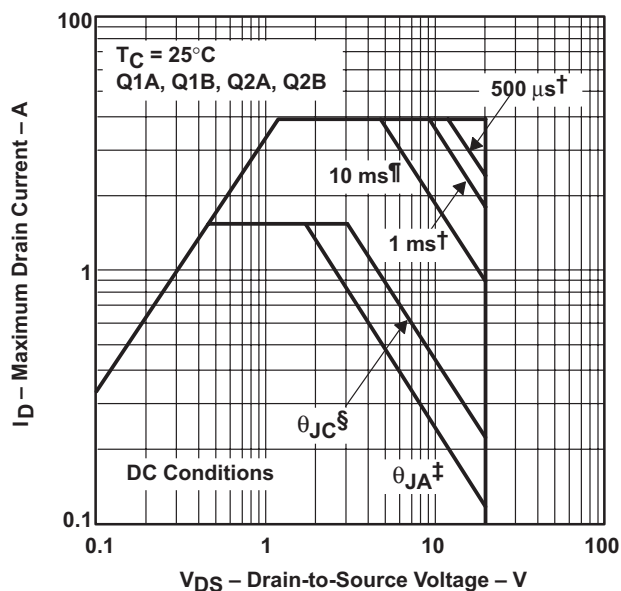


Figure 24

MAXIMUM DRAIN CURRENT vs DRAIN-TO-SOURCE VOLTAGE

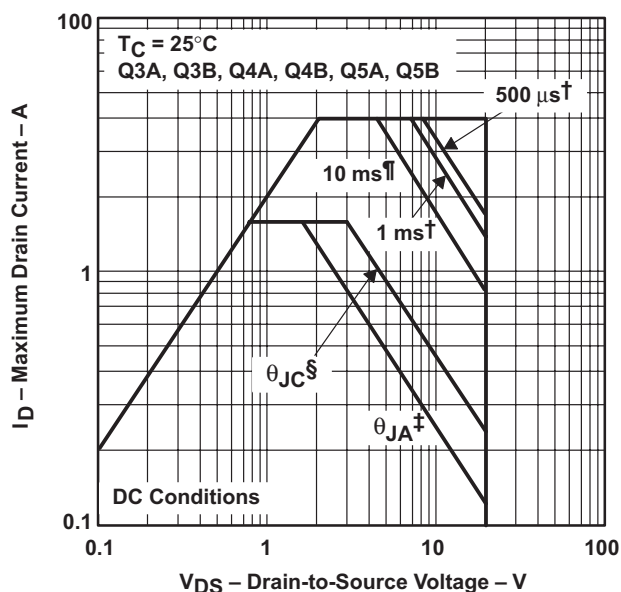


Figure 25

† Less than 10% duty cycle

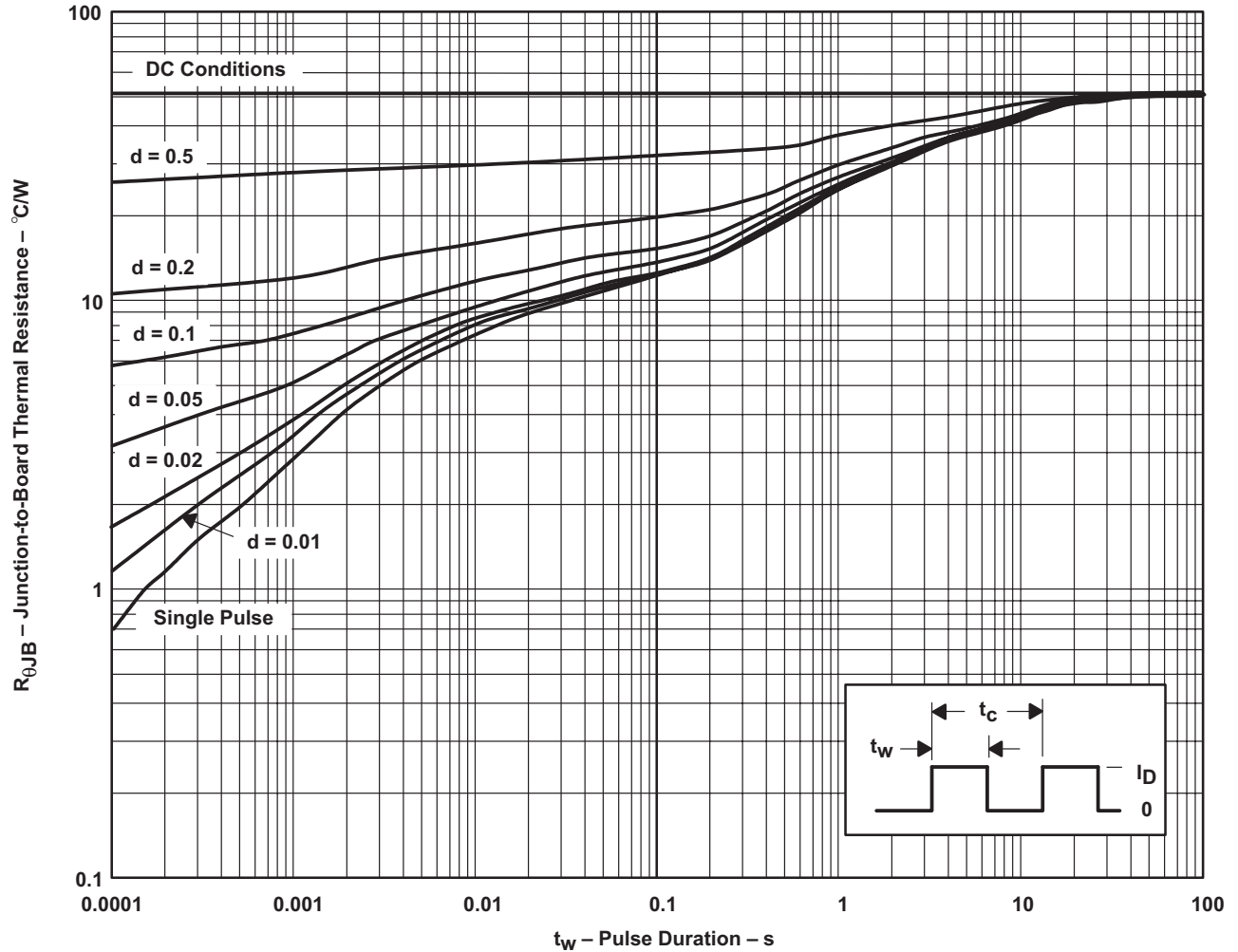
‡ Device is mounted on a 24 in², 4 layer FR4 printed-circuit board.

§ Device is mounted in intimate contact with infinite heatsink.

¶ Less than 2% duty cycle

THERMAL INFORMATION

DW PACKAGE† JUNCTION-TO-BOARD THERMAL RESISTANCE vs PULSE DURATION



† Device is mounted on 24 in², 4-layer FR4 printed circuit board with no heat sink.

NOTE A: $Z_{\theta B}(t) = r(t) R_{\theta JB}$
 t_w = pulse duration
 t_c = cycle time
 d = duty cycle = t_w/t_c

Figure 26

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